

## **Description**

The F2955 is a high reliability, low insertion loss,  $50\Omega$  SP5T absorptive RF switch designed for a multitude of RF applications, including wireless communications. This device covers a broad frequency range from 50MHz to 8000MHz. In addition to providing low insertion loss, the F2955 also delivers excellent linearity and isolation performance while providing a  $50\Omega$  termination to the unused RF input ports. The F2955 also includes a patent-pending constant impedance  $(\mathbf{K}_{|\mathbf{Z}|}^{\mathsf{TM}})$  feature.  $\mathbf{K}_{|\mathbf{Z}|}$  improves system hot switching ruggedness, minimizes LO pulling in VCOs, and reduces phase and amplitude variations in distribution networks. It is also ideal for dynamic switching/selection between two or more amplifiers while avoiding damage to upstream/downstream sensitive devices, such as power amplifiers (PAs) and analog-to-digital converters (ADCs).

The F2955 uses a single positive supply voltage supporting three logic control pins using either 3.3V or 1.8V control logic. Connecting a negative voltage to pin 20 disables the internal negative voltage generator and becomes the negative supply.

## **Competitive Advantage**

The F2955 provides constant impedance in all RF ports during transitions, improving a system's hot-switching ruggedness. The device also supports high-power handling and high isolation, particularly important for DPD receiver use.

- Constant impedance K<sub>|Z|</sub> during switching transition
- RFX to RFC isolation = 49dB at 4GHz
- Insertion loss = 1.1dB at 4GHz
- IIP3: +60.5dBm at 4GHz
- Extended temperature: -40°C to +105°C

# **Typical Applications**

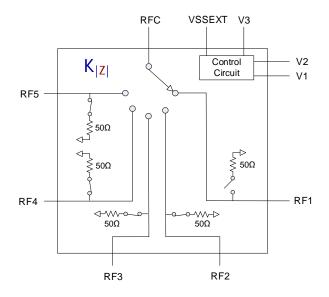
- Base Station 2G, 3G, 4G
- Portable Wireless
- Repeaters and E911 Systems
- Digital Pre-distortion
- Point-to-Point Infrastructure
- Public Safety Infrastructure
- Military Systems, JTRS Radios
- Cable Infrastructure
- Test / ATE Equipment

#### **Features**

- Five symmetric, absorptive RF ports
- High isolation: 49dB at 4000MHz
- Low insertion loss: 1.1dB at 4000MHz
- High linearity:
  - IIP2 of 114dBm at 2000MHz
  - IIP3 of 60.5dBm at 4000MHz
- High operating power handling:
  - 33dBm CW on selected RF port
  - 27dBm on terminated ports
- Single 2.7V to 5.5V supply voltage
- External negative supply option
- 3.3V and 1.8V compatible control logic
- Operating temperature: -40°C to +105°C
- 4 × 4 mm 24-QFN package
- Pin compatible with competitors

## **Block Diagram**

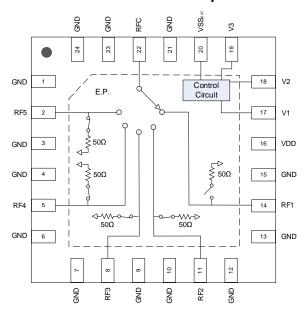
Figure 1. Block Diagram





# **Pin Assignments**

Figure 2. Pin Assignments for 4 x 4 x 0.75 mm 24-QFN - Top View



# **Pin Descriptions**

Table 1. Pin Descriptions

Number	Name	Description
1, 3, 4, 6, 7, 9, 10, 12, 13, 15, 21, 23, 24	GND	Ground these pins as close to the device as possible.
2	RF5	RF5 Port. Matched to $50\Omega$ . If this pin is not 0V DC, then an external coupling capacitor must be used.
5	RF4	RF5 Port. Matched to $50\Omega$ . If this pin is not 0V DC, then an external coupling capacitor must be used.
8	RF3	RF5 Port. Matched to $50\Omega$ . If this pin is not 0V DC, then an external coupling capacitor must be used.
11	RF2	RF5 Port. Matched to $50\Omega$ . If this pin is not 0V DC, then an external coupling capacitor must be used.
14	RF1	RF5 Port. Matched to $50\Omega$ . If this pin is not 0V DC, then an external coupling capacitor must be used.
16	$V_{DD}$	Power Supply. Bypass to GND with capacitors as shown in the "Typical Application Circuit" (Figure 39) as close as possible to the pin.
17	V1	Control pin to set the switch state. See Table 8.
18	V2	Control pin to set the switch state. See Table 8.
19	V3	Control pin to set the switch state. See Table 8.
20	VSS <sub>EXT</sub>	External VSS negative voltage control. Connect to ground to enable on-chip negative voltage generator. To bypass and disable on chip generator connect this pin to an external VSS.
22	RFC	RF Common Port. Matched to $50\Omega$ when one of the 5 RF ports is selected. If this pin is not 0V DC, then an external coupling capacitor must be used.
	EPAD	Exposed Paddle. Internally connected to GND. Solder this exposed pad to a PCB pad that uses multiple ground vias to provide heat transfer out of the device into the PCB ground planes. These multiple ground vias are also required to achieve the specified RF performance.



# **Absolute Maximum Ratings**

Stresses beyond those listed below may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Table 2. Absolute Maximum Ratings** 

Parameter	Symbol	Minimum	Maximum	Unit
V <sub>DD</sub> to GND	$V_{DD}$	-0.3	+5.5	V
V1, V2, V3 to GND	V <sub>CNTL</sub>	-0.3	Lower of (3.6,V <sub>DD</sub> +0.3)	V
RF1, RF2, RF3, RF4, RF5, RFC to GND	$V_{RF}$	-0.3	+0.3	V
VSS <sub>EXT</sub> to GND	VSS <sub>EXT</sub>	-4.0	+0.3	V
Input Power for Any One Selected RF Through Port (V <sub>DD</sub> applied at 2GHz and T <sub>EPAD</sub> = +85°C)	PMAXTHRU	-	37	dBm
Input Power for Any One Selected RF Terminated Port (V <sub>DD</sub> applied at 2GHz and T <sub>EPAD</sub> = +85°C)	PMAXTERM	-	30	dBm
Input Power for RFC When in the All Off State (V <sub>DD</sub> applied at 2GHz and T <sub>EPAD</sub> = +85°C)	Рмахсом	-	33	dBm
Continuous Power Dissipation <sup>[a]</sup> (T <sub>EPAD</sub> = +95°C Max)	P <sub>CONT</sub>	-	3	W
Maximum Junction Temperature	Тлмах	-	+125	°C
Storage Temperature Range	T <sub>ST</sub>	-65	+150	°C
Lead Temperature (soldering, 10s)	T <sub>LEAD</sub>	-	+260	°C
ESD Voltage – HBM (Per JESD22-A114)	V <sub>ESDHBM</sub>	-	1500 (Class 1C)	V
ESD Voltage – CDM (Per JESD22-C101)	V <sub>ESDCDM</sub>	-	1000 (Class C3)	V

<sup>[</sup>a]  $T_{EPAD}$  = Temperature of the exposed paddle



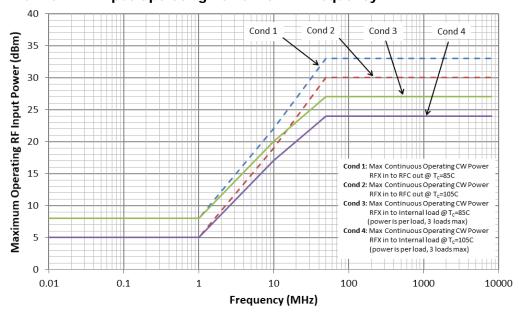
## **Recommended Operating Conditions**

**Table 3. Recommended Operating Conditions** 

Parameter	Symbol		Condition	Minimum	Typical	Maximum	Unit
	M	Pin 20 ground	Pin 20 grounded		-	5.25	
Power Supply Voltages	$V_{DD}$	Pin 20 driven	with VSS <sub>EXT</sub>	2.7	-	5.25	V
	VSS <sub>EXT</sub>	Negative supp	ıly <sup>[a]</sup>	-3.6	-3.4	-3.2	
Operating Temperature Range	T <sub>EPAD</sub>	Exposed padd	lle	-40	-	+105	°C
RF Frequency Range	f <sub>RF</sub>		-	50	-	8000	MHz
RF Continuous Input	-	Selected ports	;	-	-	33	-ID
CW Power [b]	$P_{RF}$	Terminated ports <sup>[c]</sup>		-	-	27	dBm
		DEC as the	Switch to RF1 through RF5	-	-	27	
RF Continuous Input	D	RFC as the input	Switched into or out of all off state	-	-	24	dD
CW Power for Hot RF Switching [c]	$P_{RFSW}$	RF1 through	Switched to RFC or into term <sup>[c]</sup>	-	-	27	dBm
J	RF5 as the inputs		Switch into or out of all off conditions	-	-	27	
RF1 through 5 Port Impedance	Z <sub>RFx</sub>	-		-	50	-	0
RFC Port Impedance	Z <sub>RFC</sub>		-	-	50	-	Ω

<sup>[</sup>a] For normal operation, connect VSS<sub>EXT</sub> (pin 20) = 0V to GND to enable the internal negative voltage generator. If VSS<sub>EXT</sub> is applied to pin 20, the on-chip negative voltage generator is disabled, completely eliminating any generator spurious responses.

Figure 3. Maximum CW RF Input Operating Power vs. RF Frequency



<sup>[</sup>b] Levels based on T<sub>EPAD</sub> ≤ 85°C. See Figure 3 for the power de-rating curve for higher case temperatures.

<sup>[</sup>c] In any of the insertion loss modes or when switching into any insertion loss mode, any 3 of the 4 remaining terminated port paths can be each exposed to the maximum stated power level during continuous or hot switching operation.



# **Electrical Characteristics (1)**

#### Table 4. Electrical Characteristics

Typical application circuit (Figure 39), Normal Mode ( $V_{DD} = 3.3V$ ,  $VSS_{EXT} = 0V$ ) or Bypass Mode ( $V_{DD} = 3.3V$ ,  $VSS_{EXT} = -3.3V$ ),  $T_{EPAD} = +25^{\circ}C$ ,  $f_{RF} = 2000MHz$ , input power = 0dBm,  $Z_S = Z_L = 50\Omega$ , RFX = one of the five input ports, and PCB board trace and connector losses are deembedded unless otherwise noted.

Parameter	Symbol	Coi	ndition	Minimum	Typical	Maximum	Unit
Logic Input High	V <sub>IH</sub>		-		-	Lower of (3.6, V <sub>DD</sub> )	V
Logic Input Low	VIL		-	-0.3	-	0.6	V
Logic Current	Iін, Iіц	For each contro	ol pin	-2	-	+2	μΑ
V <sub>DD</sub> DC Current	I	Normal Mode	3.3V or 1.8V logic	-	290	360	
VDD DC Current	l <sub>DD</sub>	Bypass Mode	3.3V or 1.8V logic	-	270	340	μΑ
DC Current (VSS <sub>EXT</sub> )	lvss	VSS <sub>EXT</sub> = -3.3V		-	-46	-60	μA
		f <sub>RF</sub> = 900MHz		-	0.93	1.4	
		f <sub>RF</sub> = 2100MHz		-	1.1	1.5	
Insertion Loss RFX to RFC	IL	f <sub>RF</sub> = 2700MHz		-	1.2	1.6	dB
		2700MHz < f <sub>RF</sub>	2700MHz < f <sub>RF</sub> ≤ 4000MHz		1.1	1.65	
		4000MHz < f <sub>RF</sub> ≤ 8000MHz		-	2.3	-	
Insertion Loss Flatness	IL <sub>FLAT</sub>	400MHz to 3800MHz Any 400MHz range		-	0.1	0.4	dB
		400MHz ≤ f <sub>RF</sub> ≤	900MHz	57.5	62	-	
		900MHz < f <sub>RF</sub> ≤ 2100MHz		51	55	-	dB
Minimum Isolation RFX to RFC [b][c]	ISOC	2100MHz < f <sub>RF</sub> ≤ 2700MHz		49.5	54	-	
KLV IO KLC (SIG)		2700MHz < f <sub>RF</sub> ≤ 4000MHz		45	49	-	
		4500MHz ≤ f <sub>RF</sub>	4500MHz ≤ f <sub>RF</sub> ≤ 5500MHz		44.8	-	
		400MHz ≤ f <sub>RF</sub> ≤	900MHz	56.5	59	-	
		900MHz < f <sub>RF</sub> ≤	2100MHz	50	53	-	
Minimum Isolation RFX to RFX [b][d]	ISOX	2100MHz < f <sub>RF</sub>	≤ 2700MHz	48	51	-	dB
M M M M A COLO		2700MHz < f <sub>RF</sub>	≤ 4000MHz	44.5	48	-	
		4500MHz ≤ f <sub>RF</sub>	≤ 5500MHz	41	43	-	

<sup>[</sup>a] Specifications in the minimum/maximum columns that are shown in **bold italics** are guaranteed by test. Specifications in these columns that are not shown in bold italics are guaranteed by design characterization.

<sup>[</sup>b] With one path always active.

<sup>[</sup>c] Minimum value specified for RFC to RF1 through RF4 only. Specification does not apply to RF5.

<sup>[</sup>d] Each of the 4 inputs to any other input, 4 states only, RF5 removed.



## **Electrical Characteristics (2)**

#### Table 5. Electrical Characteristics

Typical application circuit (Figure 39), Normal Mode ( $V_{DD}$  = 3.3V,  $VSS_{EXT}$  = 0V) or Bypass Mode ( $V_{DD}$  = 3.3V,  $VSS_{EXT}$  = -3.3V),  $T_{EPAD}$  = +25°C,  $f_{RF}$  = 2000MHz, input power = 0dBm,  $Z_S$  =  $Z_L$  = 50 $\Omega$ , RFX = one of the five input ports, and PCB board trace and connector losses are de-embedded unless otherwise noted.

Parameter	Symbol	Condition	Minimum	Typical	Maximum	Unit	
		400MHz ≤ f <sub>RF</sub> ≤ 900MHz	-	23	-		
		900MHz < f <sub>RF</sub> ≤ 2100MHz	-	18	-		
Minimum RFC Return Loss [b]	RLRFC	2100MHz < f <sub>RF</sub> ≤ 2700MHz	-	16	-	dB	
		2700MHz < f <sub>RF</sub> ≤ 4000MHz	-	16	-		
		4500MHz ≤ f <sub>RF</sub> ≤ 5500MHz	-	23	-		
		400MHz ≤ f <sub>RF</sub> ≤ 900MHz	-	23	-		
		900MHz < f <sub>RF</sub> ≤ 2100MHz	-	16	-		
Minimum RFX Return Loss [b] (Active Thru)	RL <sub>RFC_A</sub>	2100MHz < f <sub>RF</sub> ≤ 2700MHz	-	15	-	dB	
(rictive fillid)		2700MHz < f <sub>RF</sub> ≤ 4000MHz	-	14	-		
		4500MHz ≤ f <sub>RF</sub> ≤ 5500MHz	-	17	-		
	RL <sub>RFX_</sub> T	400MHz ≤ f <sub>RF</sub> ≤ 900MHz	-	30	-		
		900MHz < f <sub>RF</sub> ≤ 2100MHz	-	22	-	dB	
Minimum RFX Return Loss [b] (Terminated State)		2100MHz < f <sub>RF</sub> ≤ 2700MHz	-	20	-		
(Terminated State)		2700MHz < f <sub>RF</sub> ≤ 4000MHz	-	15	-		
		4500MHz ≤ f <sub>RF</sub> ≤ 5500MHz	-	14	-		
Maximum RFX Port VSWR	VCMD	From RFX Active to RFX Terminated	-	1.7:1	-		
During Switching	VSWR⊤	From RFX Terminated to RFX Active	-	2:1	-		
Input 1dB Compression [c]	ICP <sub>1dB</sub>	-	34 [a]	36.5	-	dBm	
Input 0.1dB Compression [c]	ICP <sub>0.1dB</sub>	-	28	35	-	dBm	
		$f_{RF1} = 2000 MHz$ , $f_{RF2} = 2010 MHz$ RF input = RFX, $P_{IN} = +20 dBm$ / tone $f_{RF1} + f_{RF2} = 4010 MHz$	-	114	-		
Input IP2 (Insertion Loss State)	IIP2	$f_{RF1}$ = 4900MHz, $f_{RF2}$ = 4910MHz RF Input = RFX, $P_{IN}$ = +20dBm / tone $f_{RF1}$ + $f_{RF2}$ = 9810MHz	-	106	-	dBm	
		$f_{RF1} = 5500 MHz$ , $f_{RF2} = 5510 MHz$ RF input = RFX, $P_{IN} = +20 dBm$ / tone $f_{RF1} + f_{RF2} = 11010 MHz$	-	111	-		

<sup>[</sup>a] Specifications in the minimum/maximum columns that are shown in **bold italics** are guaranteed by test. Specifications in these columns that are not shown in bold italics are guaranteed by design characterization.

<sup>[</sup>b] With one path always active.

<sup>[</sup>c] The input 0.1dB and 1dB compression points are linearity figures of merit. Refer to the "Absolute Maximum Ratings" section 0 for the maximum RF input power and for maximum operating RF input power.



# **Electrical Characteristics (3)**

#### Table 6. Electrical Characteristics

Typical application circuit (Figure 39), Normal Mode ( $V_{DD} = 3.3V$ , VSS<sub>EXT</sub> = 0V) or Bypass Mode ( $V_{DD} = 3.3V$ , VSS<sub>EXT</sub> = -3.3V), T<sub>EPAD</sub> = +25°C, f<sub>RF</sub> = 2000MHz, input power = 0dBm, Z<sub>S</sub> = Z<sub>L</sub> = 50 $\Omega$ , RFX = one of the five input ports, and PCB board trace and connector losses are de-embedded unless otherwise noted.

Parameter	Symbol	Condi	ition	Minimum	Typical	Maximum	Unit
			$f_{RF} = 400MHz$	45 [a]	60.5	-	
		Δf = 5MHz	$f_{RF} = 2000MHz$	56	60	-	
Input IP3	IIP3	RF Input = RFX	$f_{RF} = 4000MHz$	-	60.5	-	dBm
		P <sub>IN</sub> = +15dBm/tone	$f_{RF} = 4900MHz$	-	55	-	
			$f_{RF} = 5500MHz$	-	55	-	
Group Delay	GD	-		-	0.43	1	ns
	t <sub>BP-ON1</sub>	50% CTRL to 90% m	aximum RF power	-	256	345	
Switching Time – Bypass (VSS <sub>EXT</sub> = -3.3V) [b][c]	t <sub>BP-ON2</sub>	50% CTRL to RF pov ± 0.1dB of maximum		-	285	-	ns
	t <sub>BP-OFF</sub>	50% CTRL to 10% maximum RF power		-	256	345	
	t <sub>N-ON1</sub>	50% CTRL to 90% m	aximum RF power	-	245	-	
	t <sub>N-ON2</sub>	50% CTRL to RF pov ± 0.1dB of maximum		-	295	-	
Switching Time –Normal (VSS <sub>EXT</sub> = 0V) [b][c]	t <sub>N-ON3</sub>	50% CTRL to 99% RF maximum RF power		-	350	-	ns
	t <sub>n-OFF1</sub>	50% CTRL to 10% m	aximum RF power	-	200	-	
	t <sub>n-OFF2</sub>	50% CTRL to 1% ma	ximum RF power	-	245	-	
Maximum Switching Rate [d]		Pin 20 = GND		-	25	-	kHz
		Pin 20 = VSS <sub>EXT</sub> app	lied	-	290	-	KΠZ
Maximum spurious level on any RF port [e]	Spur <sub>MAX</sub>	RF ports terminated in RFX connected to RI		-	-120	-	dBm

<sup>[</sup>a] Specifications in the minimum/maximum columns that are shown in **bold italics** are guaranteed by test. Specifications in these columns that are not shown in bold italics are guaranteed by design characterization.

<sup>[</sup>b]  $f_{RF} = 1GHz$ .

<sup>[</sup>c] RFC to RFX. In and out of all-off state [000].

<sup>[</sup>d] Minimum time required between switching of states =1/ (Maximum Switching Rate).

<sup>[</sup>e] Spurious due to on-chip negative voltage generator. Typical generator fundamental frequency is 2.2MHz.



### **Thermal Characteristics**

**Table 7. Package Thermal Characteristics** 

Parameter	Symbol	Value	Unit
Junction-to-Ambient Thermal Resistance	$ heta_{JA}$	41	°C/W
Junction-to-Case Thermal Resistance (Case is defined as the exposed paddle)	θјс	6.4	°C/W
Moisture Sensitivity Rating (Per J-STD-020)		MSL1	

## **Typical Operating Conditions (TOCs)**

Unless otherwise noted for the TOC graphs on the following pages, the following conditions apply.

- $V_{DD} = 3.3V$ .
- T<sub>EPAD</sub> = +25°C (Temperature of exposed paddle).
- f<sub>RF</sub> = 2000MHz.
- RFX is the driven RF port, and RFC is the output port.
- P<sub>IN</sub> = 10dBm for all small signal tests.
- P<sub>IN</sub> = +15dBm / tone applied to selected RFX port for two-tone linearity tests.
- Two-tone frequency spacing = 5MHz.
- $Z_S = Z_L = 50\Omega$ .
- All unused RF ports terminated into 50Ω.
- For insertion loss and isolation plots, RF trace and connector losses are de-embedded (see Figure 36 for the "EVKIT Trace and Connector Loss vs. Temperature" plot).
- Plots for isolation and insertion loss over temperature and voltage are for a typical path. For performance of a specific path, refer to the online S-Parameter file.

# **Typical Performance Characteristics**

Figure 4. Insertion Loss vs. Frequency over Selected Switch

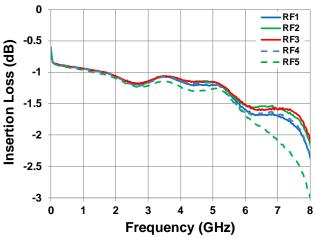


Figure 6. Insertion Loss vs. Frequency over Voltage

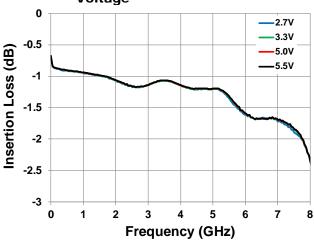


Figure 8. RFC to RFX Isolation vs. Frequency

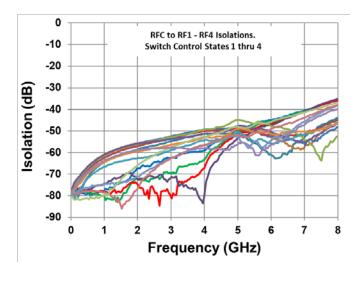


Figure 5. Insertion Loss vs. Frequency over Temperature

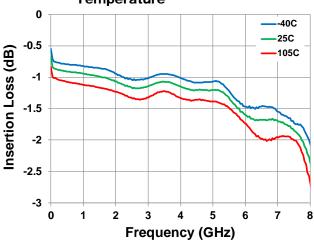


Figure 7. RFC to RFX Isolation vs. Frequency

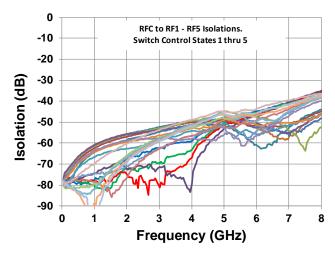


Figure 9. Typical RFC to RFX Isolation vs. Frequency over Temperature

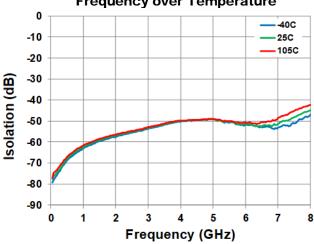


Figure 10. Typical RFC to RFX Isolation vs. Frequency over  $V_{\text{DD}}$ 

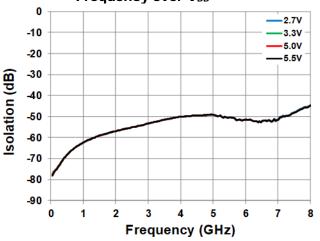


Figure 12. RFX to RFX Isolation vs. Frequency

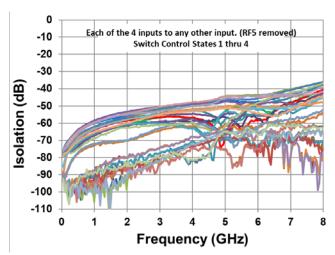


Figure 14. Typical RFX to RFX Isolation vs. Frequency over VDD

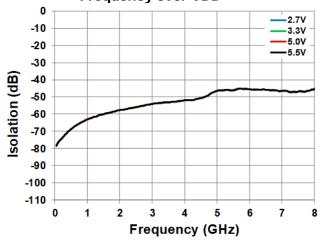


Figure 11. RFX to RFX Isolation vs. Frequency

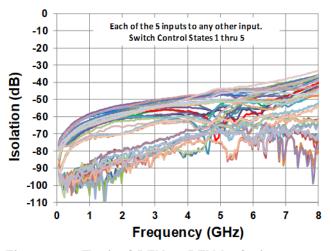


Figure 13. Typical RFX to RFX Isolation vs. Frequency over Temperature

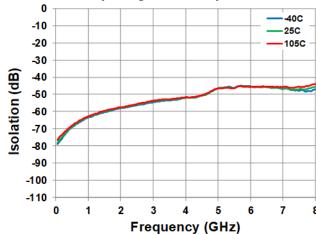


Figure 15. RFX Return Loss vs. Frequency over Switch Path [Selected State]

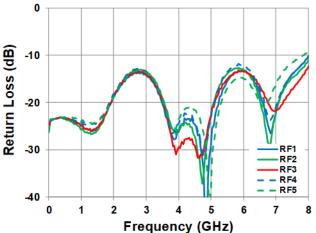


Figure 16. Typical RFX Return Loss vs. Freq. over Temp. [Selected State]

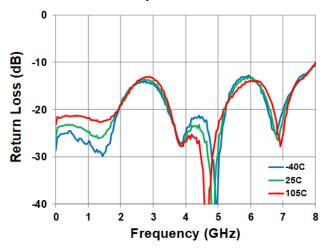


Figure 18. RFC Return Loss vs. Frequency over Switch Path [Selected State]

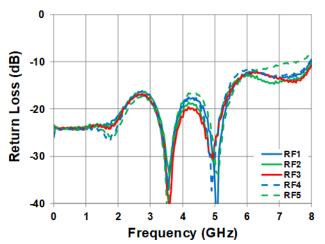


Figure 20. Typical RFC Return Loss vs. Freq. over V<sub>DD</sub> [Selected State]

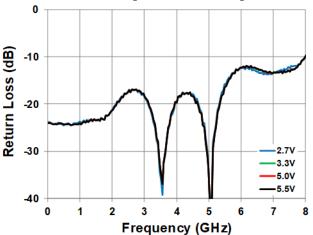


Figure 17. Typical RFX Return Loss vs. Frequency over V<sub>DD</sub> [Selected State]

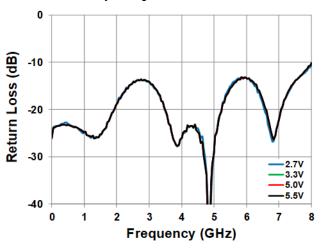


Figure 19. Typical RFC Return Loss vs. Freq. over Temp. [Selected State]

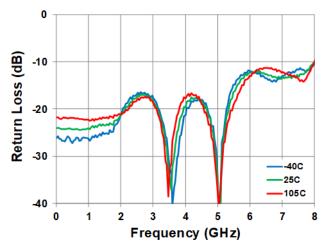


Figure 21. RFX Return Loss vs. Frequency over Switch Path [Terminated State]

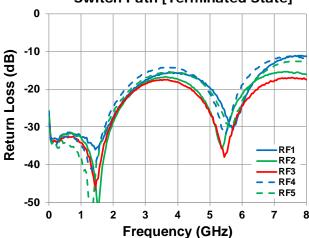


Figure 22. Typical RFX Return Loss vs. Freq. over Temp. [Terminated State]

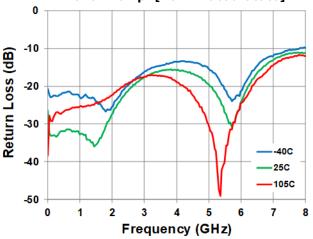


Figure 24. Return Loss (During Switching) vs. Time

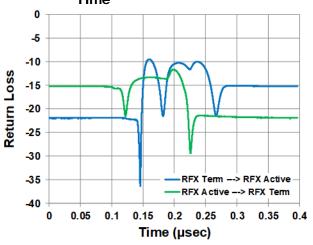


Figure 26. RFX Switching Time [RFX Terminated to RFX Active]

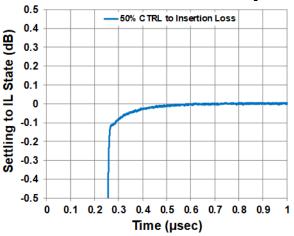


Figure 23. Typical RFX Return Loss vs. Freq. over V<sub>DD</sub> [Terminated State]

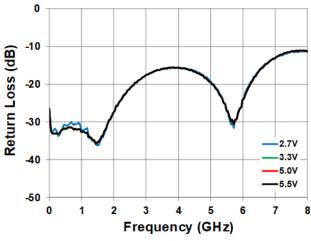


Figure 25. VSWR (During Switching) vs. Time

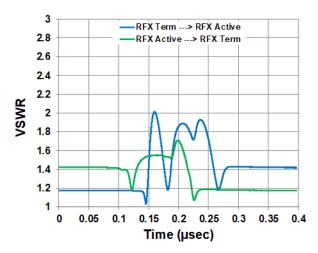


Figure 27. RFX Switching Time [RFX Active to RFX Terminated]

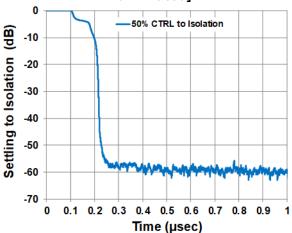


Figure 28. Switching Speed RFX to RFC All Off to On

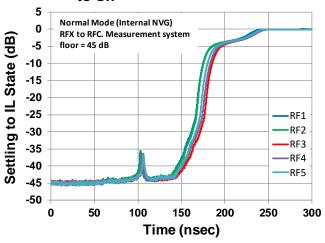


Figure 30. RFX IIP3 vs. Frequency over Switch Path [Selected State]

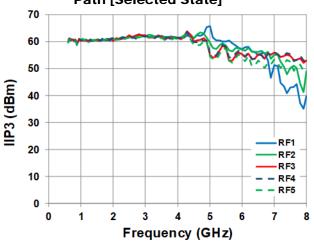


Figure 32. RF2 IIP3 vs. Frequency over Temperature and Voltage

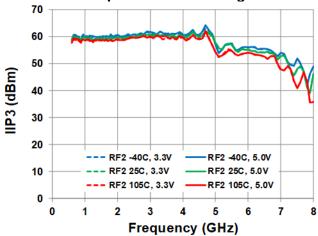


Figure 29. Switching Speed RFX to RFC On to All Off

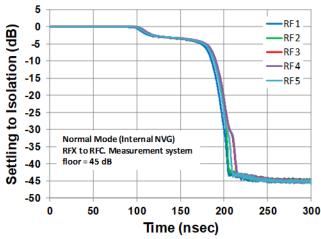


Figure 31. RF1 IIP3 vs. Frequency over Temperature and Voltage

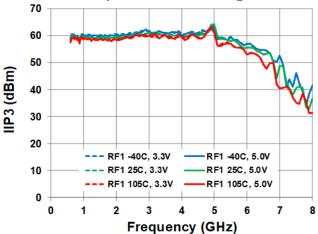


Figure 33. RF3 IIP3 vs. Frequency over Temperature and Voltage

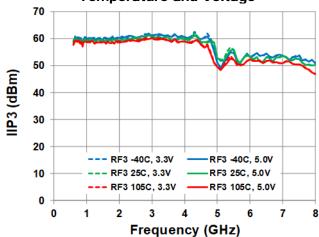


Figure 34. RF4 IIP3 vs. Frequency over Temperature and Voltage

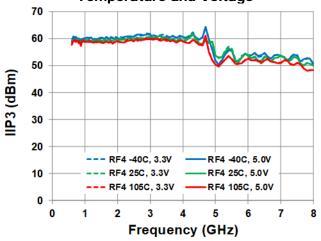


Figure 36. EVKIT Trace and Connector Loss vs. Temperature

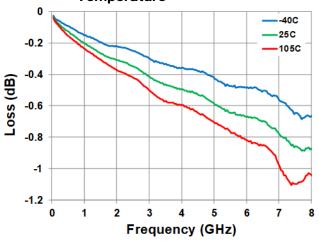
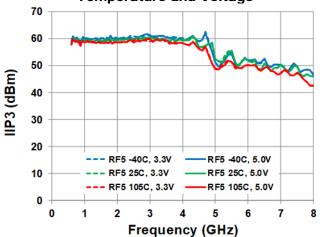


Figure 35. RF5 IIP3 vs. Frequency over Temperature and Voltage



## **Control Mode**

To select the path of the F2915 use Table 8 to see the control voltage with either 1.8V or 3.3V logic.

Table 8. Switch Control Truth Table

Mode	V3	V2	V1
All Off	0	0	0
RF1 On	0	0	1
RF2 On	0	1	0
RF3 On	0	1	1
RF4 On	1	0	0
RF5 On	1	0	1
All Off	1	1	0
All Off	1	1	1

# **Evaluation Kit Picture**

Figure 37. Top View

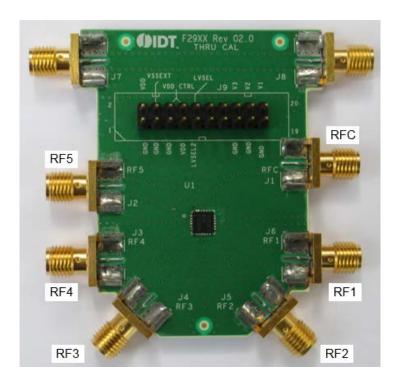
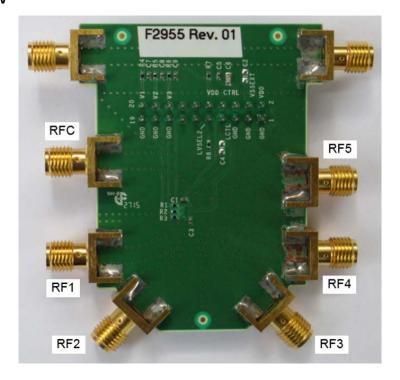


Figure 38. Bottom View





# **Evaluation Kit / Applications Circuit**

Figure 39. Electrical Schematic

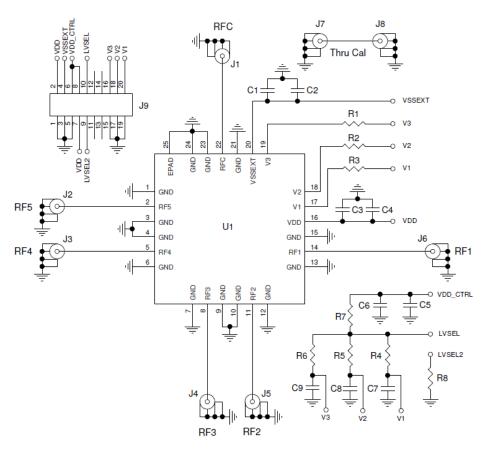


Table 9. Bill of Material (BOM)

Part Reference	QTY	Description	Manufacturer Part #	Manufacturer
C1, C3, C5, C7, C8, C9	6	100pF ±5%, 50V, C0G Ceramic Capacitor (0402)	GRM1555C1H101J	Murata
C2	0	Not Installed (0603)	-	-
C4	0	Not Installed (0603)	-	-
C6	1	1000pF ±5%, 50V, C0G Ceramic Capacitor (0603)	GRM1885C1H102J	Murata
R1, R2, R3	3	0Ω ±1%, 1/10W, Resistor (0402)	ERJ-2GE0R00X	Panasonic
R4, R5, R6	3	100kΩ ±1%, 1/10W, Resistor (0402)	ERJ-2RKF1003X	Panasonic
R7	1	15kΩ ±1%, 1/10W, Resistor (0402)	ERJ-2RKF1502X	Panasonic
R8	1	22kΩ ±1%, 1/10W, Resistor (0402)	ERJ-2RKF2202X	Panasonic
J1-J8	8	Edge Launch SMA (0.375 inch pitch ground tabs)	142-0701-851	Emerson Johnson
J9	1	CONN HEADER VERT DBL 10 X 2 POS GOLD	67997-120HLF	FCI
U1	1	SP5T Switch 4mm x 4mm QFN24-EP	F2955NBGK	Renesas (IDT)
	1	Printed Circuit Board	F29XX EVKIT Rev 02.0	Renesas (IDT)

## **Evaluation Kit (EVKit) Operation**

### **External Supply Setup**

- 1. Set up a VDD power supply in the voltage range of 2.7V to 5.5V and disable the power supply output.
- 2. If using the on-chip negative voltage generator, install a 2-pin shunt to short pins 3 (GND) and 4 (VSSEXT) of J9.
- 3. If an external negative voltage supply is to be used, set its voltage within the range of -3.6V to -3.2V and disable it. Also, ensure there are no jumper connections on pins 3 and 4 of J9.

## **Logic Control Setup**

#### Using the EVKIT to Manually Set the Control Logic

- 1. On connector J9, connect a 2-pin shunt from pin 7 (VDD) to pin 8 (VDD\_CTRL). This connection provides the VDD voltage supply to the Evaluation Board logic control pull-up network.
- On connector J9 connect a 2-pin shunt from pin 9 (LVSEL2) to pin 10 (LVSEL). This connection enables R7 (15kΩ) and R8 (22kΩ) to
  form a voltage divider to set the proper logic control levels to support the full voltage range of VDD. Note that when using the on-board
  R7 / R8 voltage divider, the current draw from the VDD supply will be higher by approximately VDD/37kΩ.
- 3. Connector J9 has 3 logic input pins: V1 (pin 20), V2 (pin 18), and V3 (pin 16). See Table 8 for the logic truth table. With the pull-up network enabled (as noted above), if these pins are left open, a logic HIGH will be provided through pull-up resistors R4, R5, and R6. To set a logic LOW to V1, V2, and V3, connect 2-pin shunts from pin 16 to pin 15, pin 18 to pin 17 and pin 20 to pin 19, respectively.

#### **Using the External Control Logic**

Pins 6, 7, 8, 9, and 10 of J9 should have no connection. External logic controls can be applied to J9 pins 16 (V3), 18 (V2) and 20 (V1). See Table 8 for the logic truth table.

#### **Turn On Procedure**

- 1. Set up the supplies and Evaluation Board as noted in "External Supply Setup" and "Logic Control Setup" above.
- 2. Connect the preset disabled VDD power supply to pin 2 (VDD) and pin 1 (GND) of J9.
- 3. If the external negative voltage source is to be used, connect the disabled supply to pin 4 (VSSEXT) and pin 3 (GND) of J9. If using the on-chip negative supply, ensure that the 2-pin shunt is installed connecting pin 3 to pin 4.
- Enable the VDD supply and then enable the VSSEXT supply (if used).
- 5. Set the desired logic setting using V1, V2, and V3 to achieve the desired path setting, see Table 8. Note that external control logic should not be applied without VDD being applied first.

#### Turn Off Procedure

- 1. If using external control logic, V1, V2, and V3 must be set to a logic LOW.
- Disable any external VSSEXT supply.
- Disable the VDD supply.

## **Application Information**

### **Default Start-up**

There are no internal pull-up or pull-down resistors on the control pins.

### **Logic Control**

Control pins V1, V2, and V3 are used to set the state of the SP5T switch (See Table 8).

#### External V<sub>ss</sub>

The F2955 is designed with an on-chip negative voltage generator. This on-chip generator is enabled by connecting pin 20 of the device to ground. To disable the on-chip generator, apply a negative voltage to pin 20 (VSS<sub>EXT</sub>) of the device within the range stated in the "Recommended Operating Conditions" (Table 3).

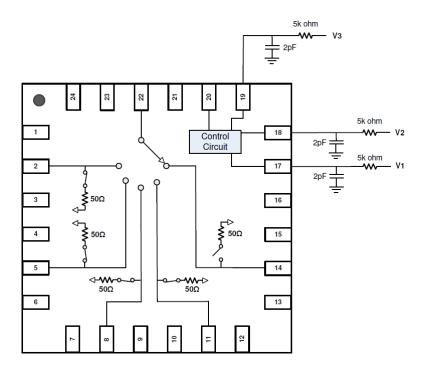
## **Power Supplies**

A common VDD power supply should be used for all pins requiring DC power. All supply pins should be bypassed with external capacitors to minimize noise and fast transients. Supply noise can degrade the noise figure, and fast transients can trigger ESD clamps and cause them to fail. Supply voltage change or transients should have a slew rate smaller than  $1V/20\mu s$ . In addition, all control pins should remain at  $0V(\pm 0.3V)$  while the supply voltage ramps or while it returns to zero.

#### **Control Pin Interface**

If control signal integrity is a concern and clean signals cannot be guaranteed due to overshoot, undershoot, ringing, etc., the following circuit at the input of each control pin is recommended. This applies to control pins 17, 18, and 19 as shown below.

Figure 40. Control Pin Interface Schematic





# **Package Outline Drawings**

The package outline drawings are located at the end of this document and are accessible from the Renesas website (see Ordering Information for POD links). The package information is the most current data available and is subject to change without revision of this document.

# **Marking Diagram**



IDTF2955 NBGK Z1528UZL Line 1 and 2 are the part number.

Line 3: "Z" is for the ASM Test Step.

Line 3: "1528" is the last two digits of the year plus the work week (YYWW).

Line 3: "UZL" denotes the Assembler Code.

# **Ordering Information**

Part Number	Package	MSL Rating	Carrier Type	Temperature Range
F2955NBGK	4.0 × 4.0 × 0.75 mm <u>24-QFN</u>	MSL1	Tray	-40°C to +105°C
F2955NBGK8	4.0 × 4.0 × 0.75 mm <u>24-QFN</u>	MSL1	Reel	-40°C to +105°C
F2955EVBK	Evaluation Board			

## **Revision History**

Date	Description of Change
November 1, 2023	Updated Block Diagram
	<ul> <li>Updated Package Outline Drawings section and added POD links in Ordering Information</li> </ul>
February 7, 2023	Updated disclaimer and POD links.
June 25, 2020	Rebranded the document as Renesas
February 21, 2019	Corrected HBM ESD voltage in Table 2
October 11, 2018	Changed maximum value for "Maximum Junction Temperature" in Table 2
	Changed maximum value for "VDD to GND" in Table 2
	<ul> <li>Updated maximum value for "Power Supply Voltages" in Table 3</li> </ul>
September 25, 2018	Initial release.

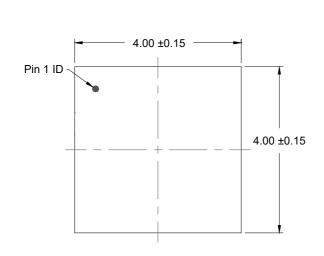
# **Package Outline Drawing**

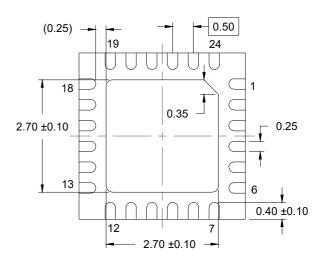


PSC-4313-03 NBG24P3

24-VFQFPN 4.0 x 4.0 x 0.75 mm Body, 0.50 mm Pitch

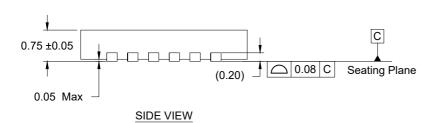
Rev.03, May 21, 2025

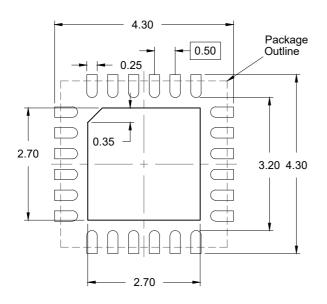




**TOP VIEW** 

**BOTTOM VIEW** 





RECOMMENDED LAND PATTERN (PCB Top View, NSMD Design)

#### NOTES:

- 1. JEDEC compatible.
- 2. All dimensions are in mm and angles are in degrees.
- 3. Use  $\pm 0.05$  mm for the non-toleranced dimensions.
- 4. Numbers in ( ) are for references only.

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